

**UNISONIC TECHNOLOGIES CO., LTD** 

### 03N50-KW

Preliminary

TO-92

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## 0.3A, 500V N-CHANNEL POWER MOSFET

#### DESCRIPTION

The UTC **03N50-KW** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.



- \* R<sub>DS(on)</sub> < 15Ω @ V<sub>GS</sub>=10V, I<sub>D</sub>=0.15A
- \* High breakdown voltage

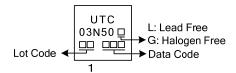
#### ORDERING INFORMATION

Ordering Number		Packago	Pin Assignment			Dooking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
03N50L-T92-B	03N50G-T92-B	TO-92	G	D	S	Tape Box	
03N50L-T92-K	03N50G-T92-K	TO-92	G	D	S	Bulk	
Note: Pin Assignment: G: Gate D: Drain S: Source							

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03N50L- <u>T92</u> -B	(1)Packing Type	(1) B: Tape Box, K: Bulk
	(2)Package Type	(2) T92: TO-92
	(3)Green Package	(3) L: Lead Free, G: Halogen Free and Lead Free

#### MARKING



#### ■ ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V <sub>DSS</sub>	500	V
Gate-Source Voltage		V <sub>GSS</sub>	±30	V
Drain Current	Continuous	Ι <sub>D</sub>	0.3	А
	Pulsed	I <sub>DM</sub>	1.2	А
Avalanche Current		I <sub>AR</sub>	0.3	А
Power Dissipation		PD	425	mW
Junction Temperature		TJ	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

#### THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ <sub>JA</sub>	180	°C/W
Junction to Case	θ」	38	°C/W

#### ■ ELECTRICAL CHARACTERISTICS (T<sub>c</sub> =25°C, unless otherwise specified)

				1		-	
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV <sub>DSS</sub>	I <sub>D</sub> =250μA, V <sub>GS</sub> =0V	500			V
Drain-Source Leakage Current		I <sub>DSS</sub>	V <sub>DS</sub> =500V, V <sub>GS</sub> =0V			10	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>	V <sub>GS</sub> =+30V, V <sub>DS</sub> =0V			+100	nA
	Reverse		V <sub>GS</sub> =-30V, V <sub>DS</sub> =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V <sub>GS(TH)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250µA	2.0		4.0	V
Static Drain-Source On-State Re	esistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.15A			15	Ω
DYNAMIC PARAMETERS							
Input Capacitance		CISS	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		74		рF
Output Capacitance		C <sub>OSS</sub>			12.7		рF
Reverse Transfer Capacitance		C <sub>RSS</sub>			4.6		рF
SWITCHING PARAMETERS							
Total Gate Charge		$Q_{G}$	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 0.3A, I <sub>D</sub> =100µA (Note 1, 2)		7.84		nC
Gate to Source Charge		Q <sub>GS</sub>			0.94		nC
Gate to Drain Charge		$Q_{GD}$	$I_{\rm D}$ = 100 $\mu$ A (Note 1, 2)		0.55		nC
Turn-ON Delay Time		t <sub>D(ON)</sub>			50		ns
Rise Time		t <sub>R</sub>	$V_{DS}$ = 30V, $V_{GS}$ = 10V, $I_D$ = 0.3A, R <sub>G</sub> = 25 $\Omega$ (Note 1, 2)		17.8		ns
Turn-OFF Delay Time		t <sub>D(OFF)</sub>			44		ns
Fall-Time		t <sub>F</sub>			28.2		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuo	us Current	ls				0.3	Α
Maximum Body-Diode Pulsed Current		I <sub>SM</sub>				1.2	Α
Drain-Source Diode Forward Voltage		$V_{SD}$	I <sub>S</sub> =0.3A, V <sub>GS</sub> =0V			1.4	V

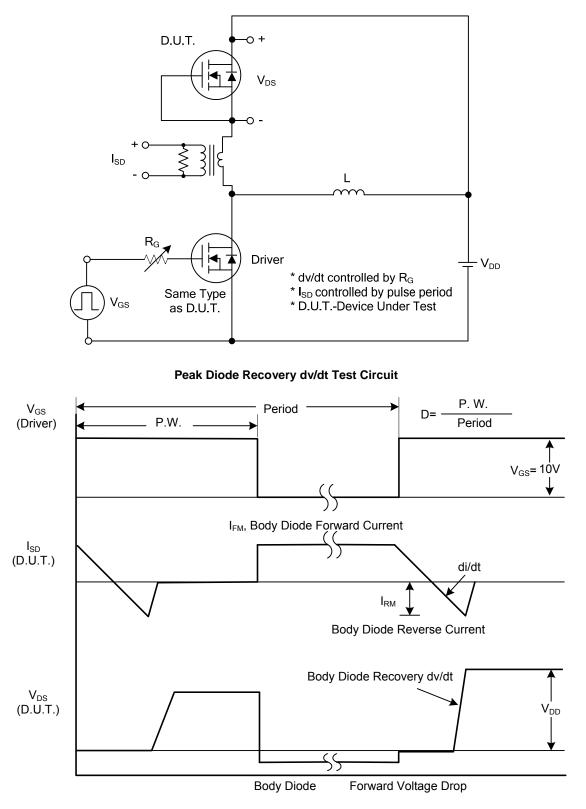
Notes: 1. Pulse Test: Pulse width  $\leq$  300µs, Duty cycle  $\leq$  2%.

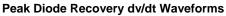
2. Essentially independent of operating temperature.



# 03N50-KW

#### TEST CIRCUITS AND WAVEFORMS







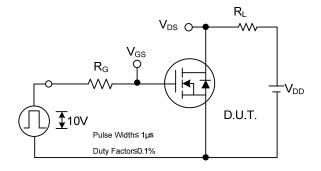
# 03N50-KW

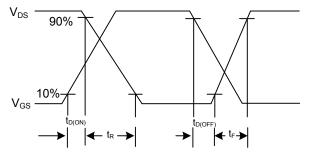
 $\mathsf{V}_{\mathsf{GS}}$ 

10V

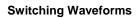
Q<sub>GS</sub>

### ■ TEST CIRCUITS AND WAVEFORMS (Cont.)



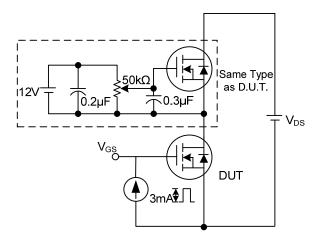


#### Switching Test Circuit

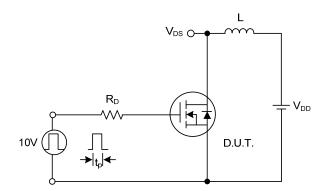


 $\mathsf{Q}_\mathsf{G}$ 

 $\mathsf{Q}_{\mathsf{GD}}$ 



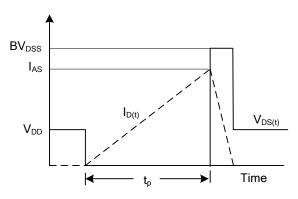
**Gate Charge Test Circuit** 



**Unclamped Inductive Switching Test Circuit** 

**Gate Charge Waveform** 

Charge



**Unclamped Inductive Switching Waveforms** 



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